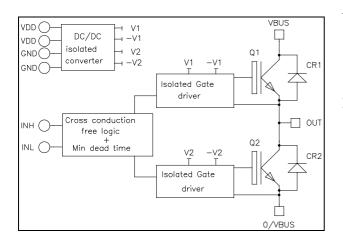
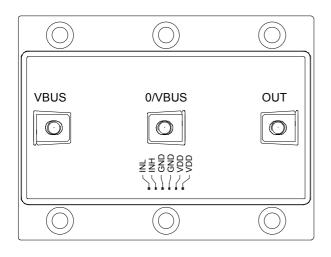


Phase leg Intelligent Power Module





APTLGT400A608G

$V_{CES} = 600V$

 $I_{\rm C} = 400 {\rm A}$ @ Tc = 80°C

Application

- Motor control
- Uninterruptible Power Supplies
- Switched Mode Power Supplies
- Amplifier
- Features
 - Non Punch Through (NPT) FAST IGBT
 - Low voltage drop
 - Low tail current
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA & SCSOA rated
 - Integrated Fail Safe IGBT Protection (Driver)
 - Top Bottom input signals Interlock
 - Isolated DC/DC Converter
 - Low stray inductance
 - M5 power connectors
 - High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Very high noise immunity (common mode rejection > 25kV/µs)
- Galvanic Isolation: 3750V for the optocoupler 2500V for the transformer
- 5V logic level with Schmitt-trigger Input
- Single V_{DD} =5V supply required
- Secondary auxiliary power supplies internally generated (15V, -6V)
- Optocoupler qualified to AEC-Q100 test guidelines
- RoHS compliant

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

1. Inverter Power Module

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		600	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	600	
I _C	Continuous Conector Current $T_c =$		400	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	800	
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1250	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	800A@550V	

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_j = 25^{\circ}C$			0.3	mA
		$V_{CE} = 600V$	$T_{j} = 150^{\circ}C$			1	mA
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{DD} = V_{IN} = 5V$	$T_j = 25^{\circ}C$		1.5	1.9	V
		$I_{\rm C} = 400 {\rm A}$	$T_{j} = 150^{\circ}C$		1.7		v

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		24		
C _{oes}	Output Capacitance	$V_{CE} = 25V$		1.6		nF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz		0.8		
T _r	Rise Time	Inductive Switching (25°C) $V_{c} = V_{c} = 5V_{c}$		45		ns
$T_{\rm f}$	Fall Time	$V_{DD} = V_{IN} = 5V$ $V_{Bus} = 300V$; $I_C = 400A$		55		ns
T _r	Rise Time	Inductive Switching (125°C)		25		20
$T_{\rm f}$	Fall Time	$V_{DD} = V_{IN} = 5V$		70		ns
Eon	Turn-on Switching Energy	$V_{Bus} = 300V$ $I_C = 400A$		3.5		T
E_{off}	Turn-off Switching Energy			14		mJ
I _{sc}	Short Circuit data	$V_{DD} = V_{IN} = 5V; V_{Bus} = 360V$ $t_p \le 6\mu s; T_j = 150^{\circ}C$		2000		А
R _{thJC}	Junction to Case thermal resistance				0.12	°C/W



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Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_i = 25^{\circ}C$			350	μA
-KW			$T_{i} = 150^{\circ}C$			500	P*
I _F	DC Forward Current		$Tc = 80^{\circ}C$		400		Α
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 400 {\rm A}$	$T_i = 25^{\circ}C$		1.6	2	V
• F	Diode i of ward Voltage		$T_{i} = 150^{\circ}C$		1.5		v
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		125	n	ns
•11		$T_j = 150^{\circ}C$		220		115	
Q _{rr}	Reverse Recovery Charge	$I_F = 400A$ $V_R = 300V$ $di/dt = 4800A/\mu s$	$T_j = 25^{\circ}C$		19		μC
Qrr	Reverse Recovery charge		$T_{j} = 150^{\circ}C$		40		μΟ
Б			$T_j = 25^{\circ}C$		4.4		mJ
E _{rr}	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		9.6		111J
R _{thJC}	Junction to Case thermal resistance					0.20	°C/W

2. Driver

Absolute maximum ratings

Symbol	<i>F</i>	Parameter	Max ratings	Unit
V_{DD}	Supply Voltage		5.5	V
V _{INi}	Input signal voltage i=L, H		5.5	v
I _{VDDmax}	Waximum Nunniv current	$V_{INi} = 0V, i = L \& H$	0.35	٨
		$V_{DD}=5V$, $V_{INH}=/V_{INL}$; $F_{out}=45kHz$	2	A
f _{max}	Maximum Switching Frequence	су.	45	kHz

Driver Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
V _{DD}	Operating Supply Voltage		4.5	5	5.5	V
V _{INi(max)}	Maximum Input Voltage		-0.5	5	5.5	
V _{INi (th+)}	Positive Going Threshold Voltage	i = L. H		3.2		V
V _{INi(th-)}	Negative Going Threshold Voltage	1 L, 11		1		
R _{INi}	Input Resistance *	1		1		kΩ
T _{d(on)}	Turn On delay time	Driver + IGBT		1100 0		
D _T	Built in dead time			600		ns
T _{d(off)}	Turn Off delay time	Driver + IGBT		750		
PWD	Pulse Width Distortion				300	
PDD	Propagation Delay Difference	T _{d(on)} - T _{d(off)}	-350		350	ns
100	between any two driver	a(on) d(on)	550		550	
V _{ISOL}	Primary to Secondary Isolation		2500			V _{RMS}

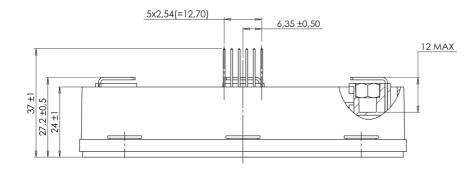
* Low impedance guarantees good noise immunity.

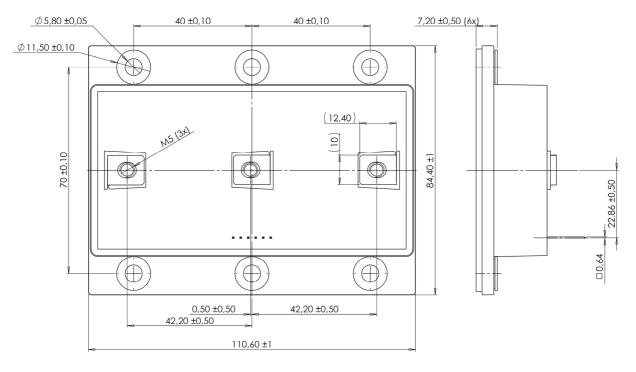


3. Package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =	1 min, 50/60Hz		4000			V		
T _J	Operating junction temperature range -40 150				150				
T _{OP}	Operating Ambient Temperature			-40		85	°C		
T _{STG}	Storage Temperature Range			-40		100			
T _C	Operating Case Temperature		-40		100				
Torqua	Mounting torque To heatsink M5 For terminals M5	To heatsink	M5	2		4.7	N.m		
Torque		M5	2		4	IN.III			
Wt	Package Weight				550		g		

4. LP8 Package outline (dimensions in mm)

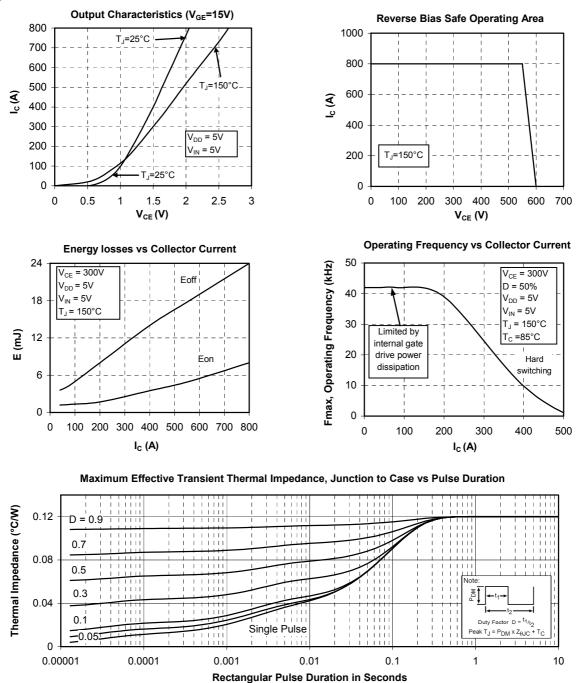






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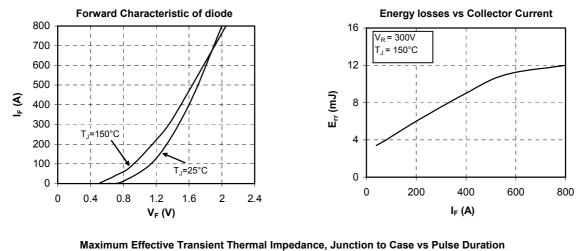
Typical IGBT Performance Curve

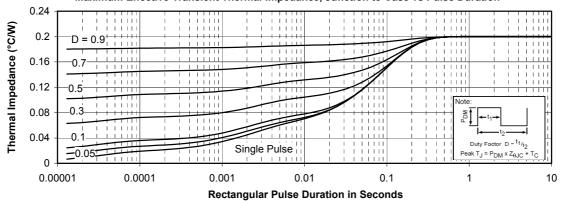


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Typical diode Performance Curve







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